

N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

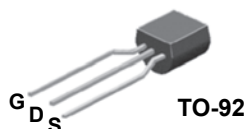
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
60	0.030 at $V_{GS} = 10$ V	8.0
	0.036 at $V_{GS} = 4.5$ V	6.5

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available



TO-92



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V_{DS}	60		V
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 175$ °C) ^a	I_D	8.0	7.0	A
		6.4	5.6	
Pulsed Drain Current	I_{DM}	40		
Avalanche Current	I_{AS}	15		
Single Pulse Avalanche Energy	E_{AS}	11		mJ
Maximum Power Dissipation ^a	P_D	3.3	1.7	W
		2.3	1.2	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175		°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	36	45	°C/W
		75	90	
Maximum Junction-to-Foot (Drain)	R_{thJF}	17	20	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

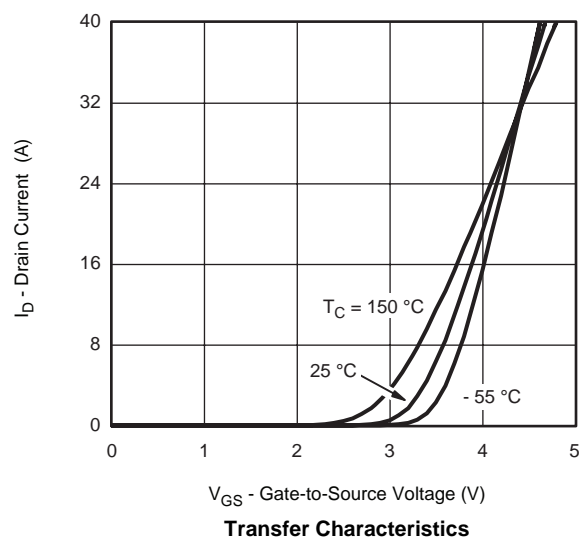
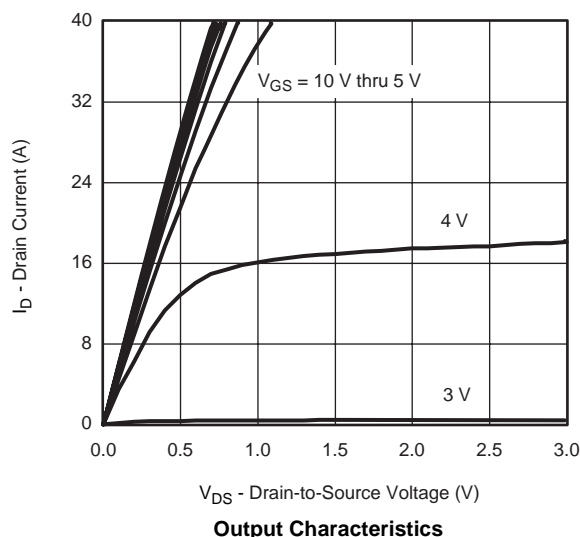
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1		3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^\circ\text{C}$			20	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$	40			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 6.0\text{ A}$		0.030		Ω
		$V_{GS} = 10\text{ V}$, $I_D = 6.0\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$		0.035		
		$V_{GS} = 10\text{ V}$, $I_D = 6.0\text{ A}$, $T_J = 175\text{ }^\circ\text{C}$		0.040		
		$V_{GS} = 4.5\text{ V}$, $I_D = 5.1\text{ A}$		0.036		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 6.0\text{ A}$		25		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 1.7\text{ A}$, $V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 6.0\text{ A}$		18	27	nC
Gate-Source Charge	Q_{gs}			3.4		
Gate-Drain Charge	Q_{gd}			5.3		
Gate Resistance	R_g	$V_{GS} = 0.1\text{ V}$, $f = 5\text{ MHz}$	0.5	1.4	2.4	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}$, $R_L = 30\text{ }\Omega$ $I_D \cong 1\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 6\text{ }\Omega$		10	20	ns
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(off)}$			25	50	
Fall Time	t_f			12	24	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		50	80	

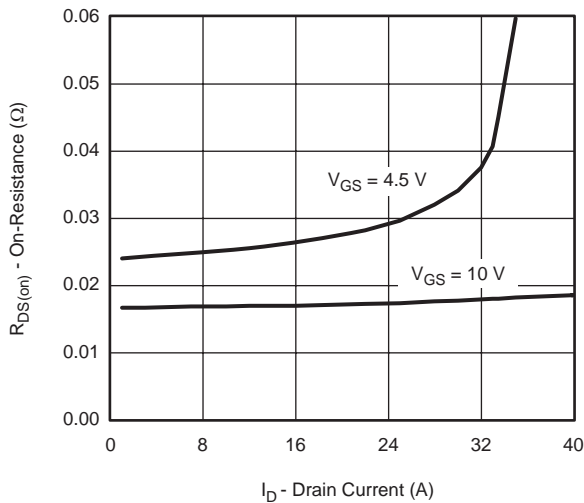
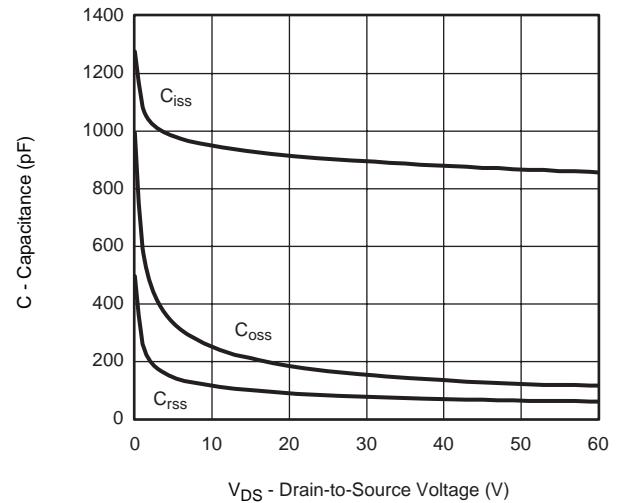
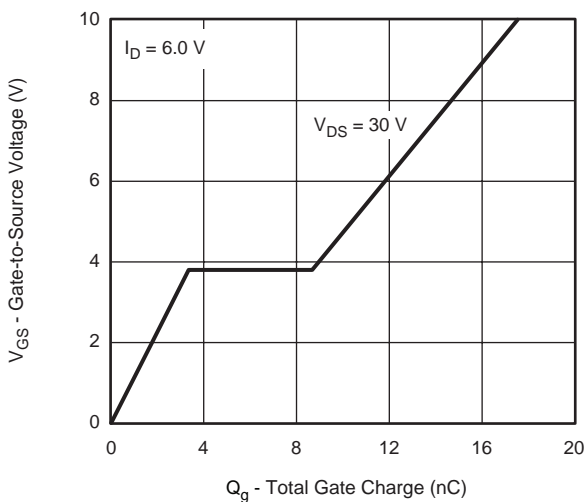
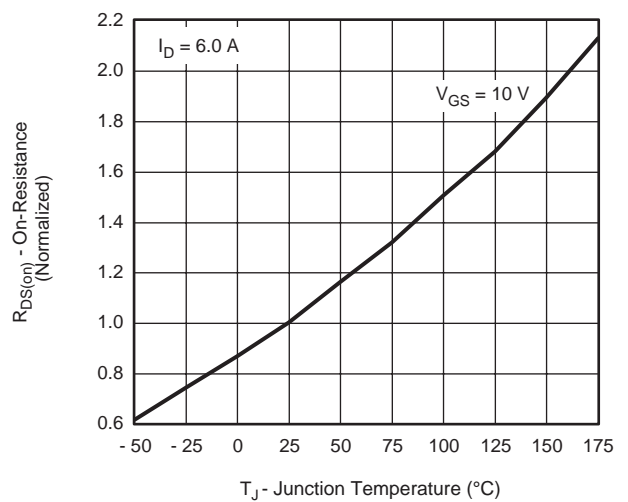
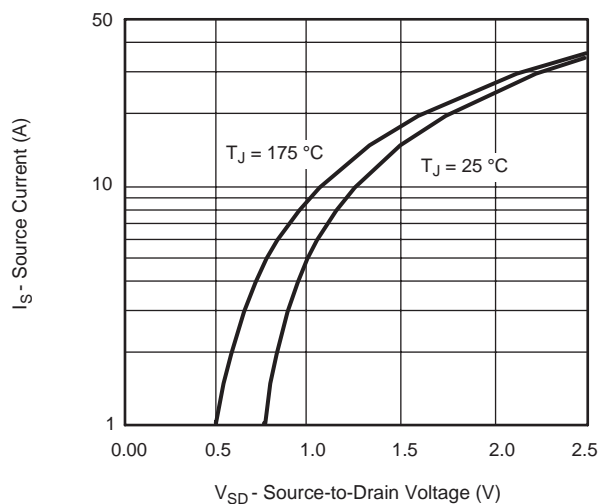
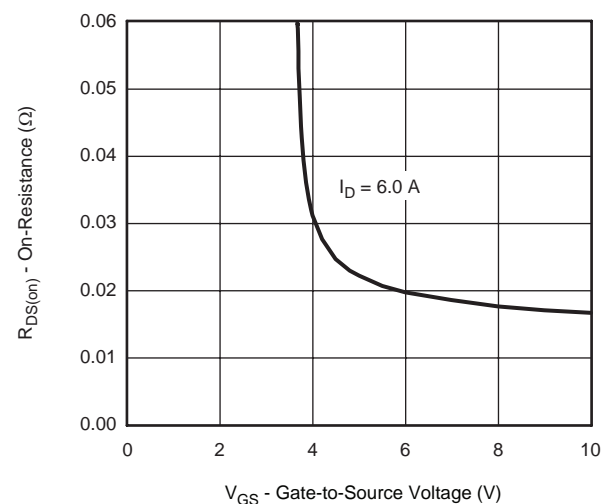
Notes:

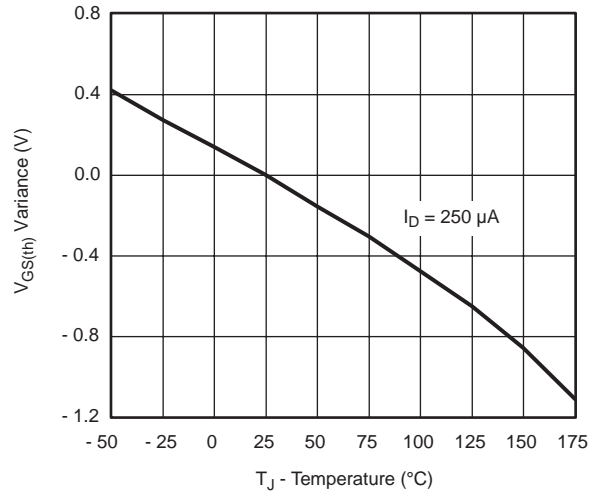
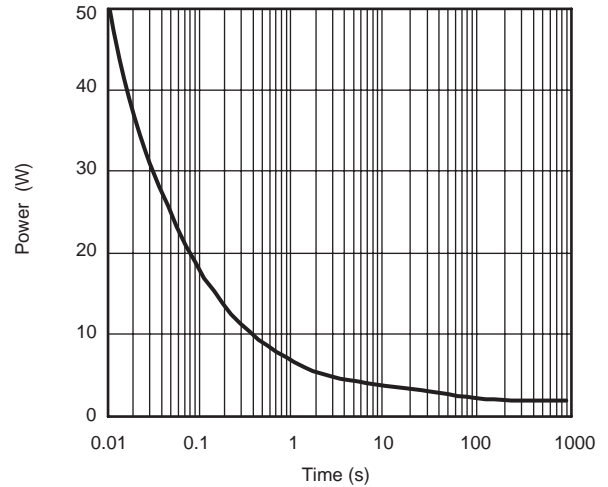
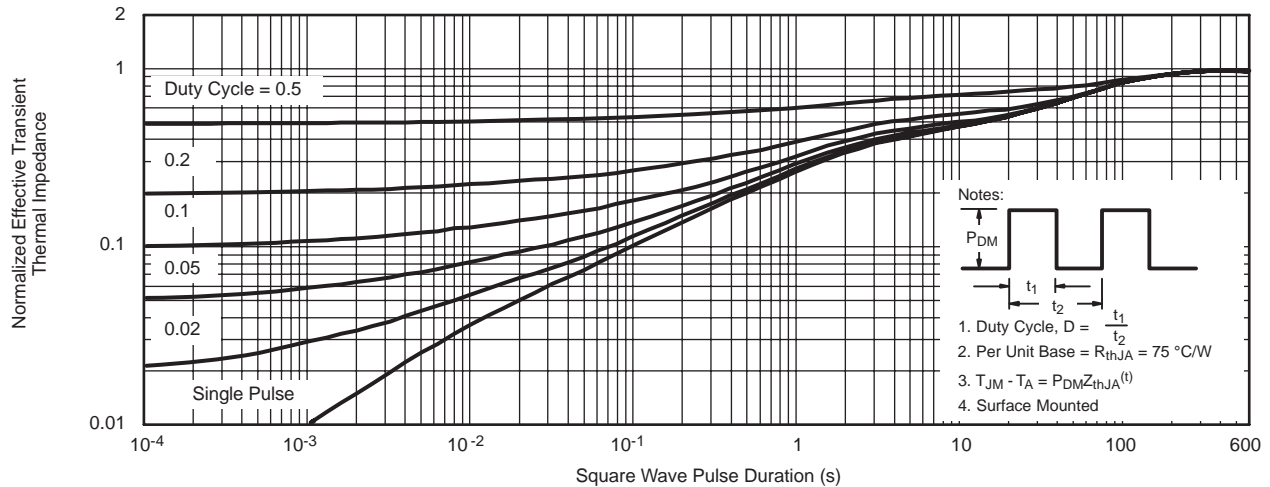
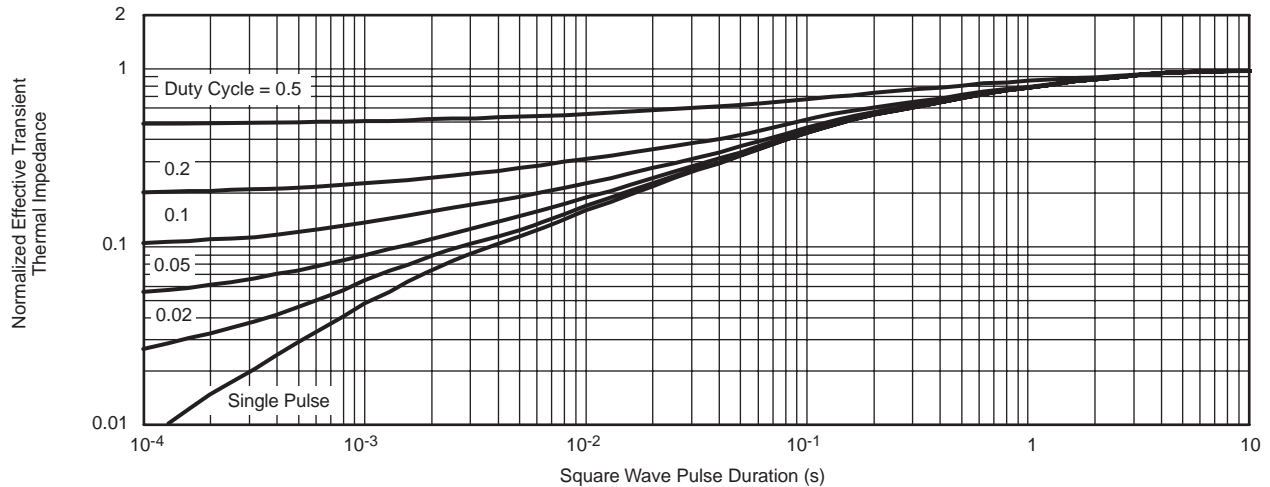
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

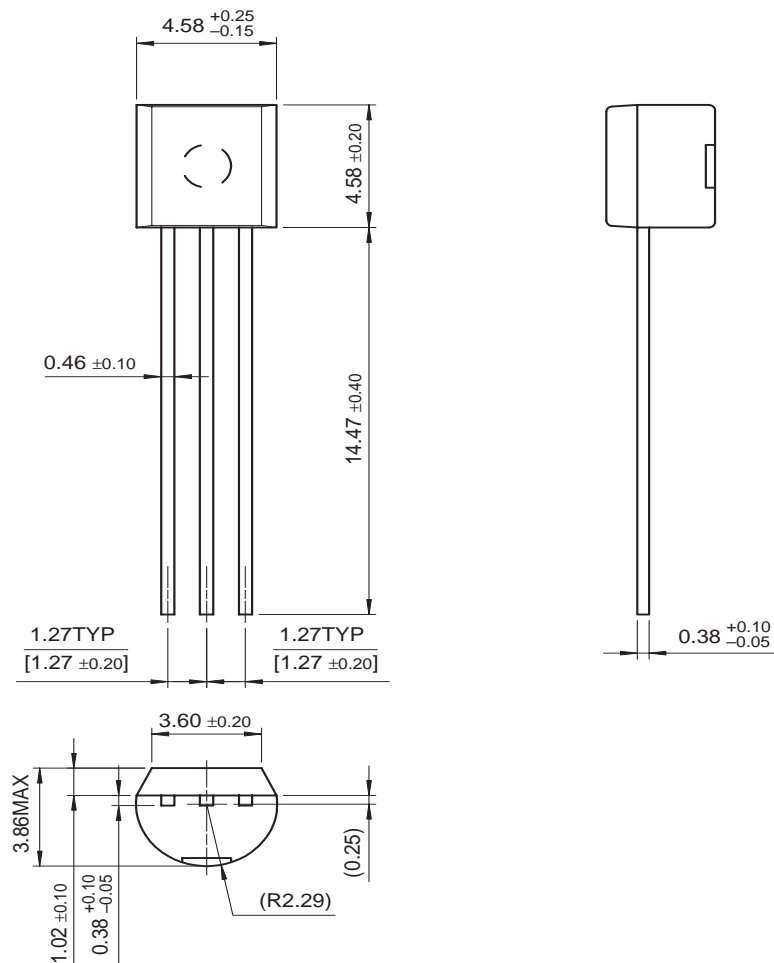
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Threshold Voltage

Single Pulse Power

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Foot

Mechanical Dimensions

TO-92



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